IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Cheng, *et al.*	Docket No.:	TSM03-0698
Filed:	2/25/2004	Examiner:	Kevin Quinto
Serial No.:	10/786,643	Art Unit:	2826
Title:	CMOS Structure and Related Method		

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Respectfully submitted,

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For:	CMOS Structure and Related Method		

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Sheet	1	of	6

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U.S. PATENT DOCUMENTS

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	1	US-4,069,094	01-17-1978	Shaw et al.	
	2	US-4,314,269	02-02-1982	Fujiki	
	3	US-4,497,683	02-05-1985	Celler et al.	
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Art Unit	2826
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Attorney Docket Number	TSM03-0698

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Sheet 3 of 6

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Application Number	10/786,643
Filing Date	2/25/2004
First Named Inventor	Cheng, *et al.*
Art Unit	2826
Examiner Name	Quinto, Kevin
Attorney Docket Number	TSM03-0698

FOREIGN PATENT DOCUMENTS

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NON PATENT LITERATURE DOCUMENTS

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Sheet 4 of 6

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	83	CHANG, L., *et al.*, "Direct-Tunneling Gate Leakage Current in Double-Gate and Ultrathin Body MOSFETs," 2002 IEEE Transactions on Electron Devices, Vol. 49, No. 12, December 2002, pp. 2288-2295.	
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Sheet 5 of 6

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